

Taiwan Semiconductor

25A, 45V - 150V Schottky Barrier Rectifier

FEATURES

- Low power loss, high efficiency
- Guard ring for overvoltage protection
- High surge current capability
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

APPLICATIONS

- Switching mode power supply (SMPS)
- Adapters
- DC to DC converters

MECHANICAL DATA

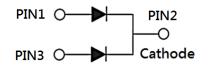
- Case: TO-220AB
- Molding compound meets UL 94V-0 flammability rating
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Mounting torque: 0.56 N·m maximum
- Meet JESD 201 class 1A whisker test
- Polarity: As marked
- Weight: 1.90g (approximately)

KEY PARAMETERS		
PARAMETER	VALUE	UNIT
١ _F	25	А
V _{RRM}	45 - 150	V
I _{FSM}	200	А
T _{J MAX}	150	°C
Package	TO-220AB	
Configuration	Dual d	lies









ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)							
DADAMETED	CVMDOI	MBR	MBR	MBR	MBR		
PARAMETER	SYMBOL	2545CT-Y	2560CT-Y	25100CT-Y	25150CT-Y	UNIT	
Marking and an the device		MBR	MBR	MBR	MBR		
Marking code on the device		2545CT	2560CT	25100CT	25150CT		
Repetitive peak reverse voltage	V _{RRM}	45	60	100	150	V	
Reverse voltage, total rms value	V _{R(RMS)}	31	42	70	105	V	
Forward current	I _F	25		Α			
Surge peak forward current, 8.3ms							
single half sine wave	I _{FSM}		2	00		Α	
superimposed on rated load							
Peak repetitive reverse	1	- 1		0.5		А	
surge current ⁽¹⁾	I _{RRM}	I.		0.5		A	
Peak repetitive forward current	1		,	25		А	
(Rated V _R , Square wave, 20KHz)	I _{FRM}		4	20		A	
Critical rate of rise of off-state voltage	dv/dt	10,000		V/µs			
Junction temperature	TJ	-55 to +150		°C			
Storage temperature	T _{STG}	-55 to +150		°C			

Notes:

1. tp = 2.0µs, 1.0KHz



THERMAL PERFORMANCE			
PARAMETER	SYMBOL	ТҮР	UNIT
Junction-to-case thermal resistance	R _{eJC}	1	°C/W

ELECTRICAL SP	ECIFICATION	IS ($T_A = 25^{\circ}C$ unless other	erwise noted)			I
PARAMETER		CONDITIONS	SYMBOL	ΤΥΡ	MAX	UNIT
	MBR2545CT-Y	I _F = 12.5A, T _J = 25°C	-	-	-	V
	MBR2560CT-Y			-	0.75	V
	MBR25100CT-Y			-	0.85	V
	MBR25150CT-Y			-	0.95	V
	MBR2545CT-Y			-	0.82	V
	MBR2560CT-Y			-	-	V
	MBR25100CT-Y	Ι _F = 25.0A, Τ _J = 25°C			0.92	V
Forward voltage per	MBR25150CT-Y		V	-	1.02	V
diode ⁽¹⁾	MBR2545CT-Y		V _F	-	-	V
	MBR2560CT-Y	I _F = 12.5A, T _J = 125°C		-	0.65	V
	MBR25100CT-Y			-	0.75	V
	MBR25150CT-Y			-	0.92	V
	MBR2545CT-Y			-	0.73	V
	MBR2560CT-Y	I _F = 25.0A, T _J = 125°C		-	-	V
	MBR25100CT-Y				0.88	V
	MBR25150CT-Y			-	0.98	V
Reverse current @ rated V_B per diode ⁽²⁾	MBR2545CT-Y MBR2560CT-Y	T _J = 25°C	I _R	-	200	μA
	MBR25100CT-Y MBR25150CT-Y	1j=23 0		-	100	μΑ
	MBR2545CT-Y			-	15	mA
Tated VR per diode	MBR2560CT-Y	T _J = 125°C		-	10	mA
	MBR25100CT-Y			-	7.5	mA
	MBR25150CT-Y			-	5	mA

Notes:

1. Pulse test with PW = 0.3ms

2. Pulse test with PW = 30ms

ORDERING INFORMATION		
ORDERING CODE ⁽¹⁾	PACKAGE	PACKING
MBR25xCT-Y	TO-220AB	50 / Tube

Notes:

1. "x" defines voltage from 45V(MBR2545CT-Y) to 150V(MBR25150CT-Y)



MBR2545CT-Y – MBR25150CT-Y

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CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

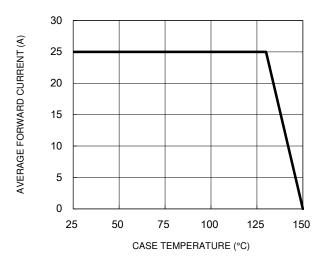


Fig.1 Forward Current Derating Curve

Fig.3 Typical Reverse Characteristics

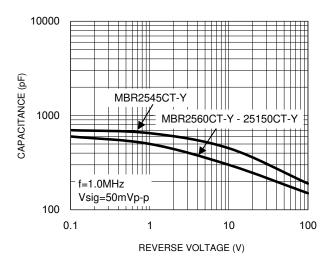
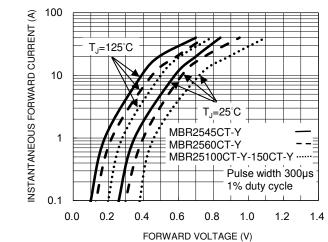


Fig.4 Typical Forward Characteristics



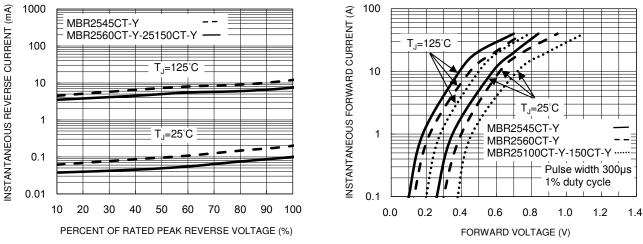


Fig.5 Maximum Non-Repetitive Forward Surge Current

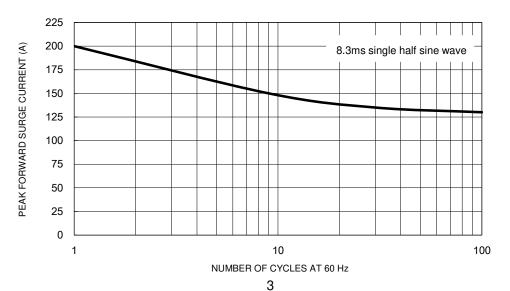


Fig.2 Typical Junction Capacitance



CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

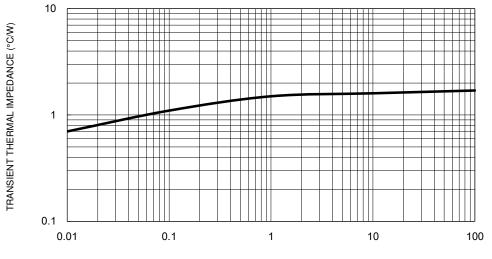
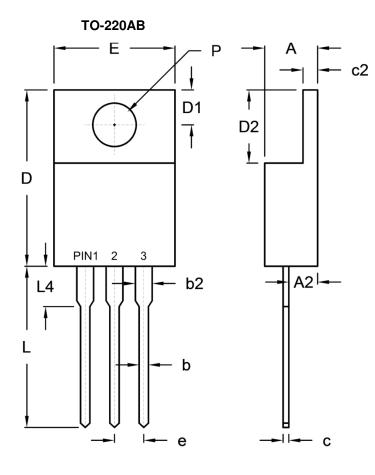


Fig.6 Typical Transient Thermal Impedance

PULSE DURATION (s)

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PACKAGE OUTLINE DIMENSIONS



DIM.	Unit (mm)		Unit ((inch)
	Min.	Max.	Min.	Max.
A	4.42	4.76	0.174	0.187
A2	2.20	2.80	0.087	0.110
b	0.68	0.94	0.027	0.037
b2	1.14	1.77	0.045	0.070
с	0.35	0.64	0.014	0.025
c2	1.14	1.40	0.045	0.055
D	14.60	16.00	0.575	0.630
D1	2.62	3.44	0.103	0.135
D2	5.84	6.86	0.230	0.270
E	-	10.50	-	0.413
е	2.41	2.67	0.095	0.105
L	13.19	14.79	0.519	0.582
L4	2.80	4.20	0.110	0.165
Р	3.54	4.00	0.139	0.157

MARKING DIAGRAM



P/N	= Marking Code
G	= Green Compound
YWW	= Date Code
F	= Factory Code



MBR2545CT-Y – MBR25150CT-Y

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